1-37. (Cancelled)

38. (Currently Amended) A process for fabricating a semiconductor device, comprising the steps of attaching a semiconductor chip to a support member with a die-bonding material, and encapsulating the semiconductor chip with a resin;

said die-bonding material comprising a filmy die-bonding material comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, [[and]] polyimide resin~~; resin, polyimide resin~~ and epoxy resin;

the process further comprising the steps of:

mounting said semiconductor chip on said filmy die-bonding material; and

attaching said semiconductor chip to said filmy die-bonding material under conditions of a temperature of 150°C to 250°C, bonding time of 0.1 (inclusive) second to 2 seconds, and a pressure of 0.1 to 4 gf/mm^2.

39-48. (Cancelled)

49. (Currently Amended) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material ~~comprising polyimide and epoxy resin~~ comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin; and

said filmy die-bonding material has a water absorption of 1.5% by volume or less.

50. (Previously Presented) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material

comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin; and

said filmy die-bonding material has a residual volatile component in an amount not more than 3.0% by weight.

51. (Currently Amended) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material ~~comprising polyimide and epoxy resin~~ comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin; and

said filmy die-bonding material has a modulus of elasticity of 10 Mpa or less at a temperature of 250°C.

52. (Currently Amended) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material ~~comprising polyimide and epoxy resin~~ comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, [[and]] polyimide resin~~, resin, polyimide resin~~ and epoxy resin; and

said filmy die-bonding material having, at a stage where the semiconductor chip has been bonded to the support member, a void volume of 10% or less in terms of voids present in the die-bonding material and at an interface between the die-bonding material and the support member.

53. (Currently Amended) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material ~~comprising polyimide and epoxy resin~~ comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin; and

said filmy die-bonding material has a peel strength of 0.5 kgf/5 x 5 mm chip or above at a stage where the semiconductor chip has been bonded to the support member.

54. (Previously Presented) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin; and

said filmy die-bonding material i) has a planar dimension not larger than a planar dimension of the semiconductor chip, and ii) not protruding outward from a region of the semiconductor chip at a stage where the semiconductor chip has been bonded to the support member.

55-62. (Cancelled)

63. (New) A process according to claim 38, wherein said filmy die-bonding material comprises polymide resin and epoxy resin.

64. (New) A process according to claim 49, wherein said filmy die-bonding material comprises polymide resin and epoxy resin.

65. (New) A process according to claim 50, wherein said filmy die-bonding material comprises polymide resin and epoxy resin.

66. (New) A process according to claim 51, wherein said filmy die-bonding material comprises polymide resin and epoxy resin.

67. (New) A process according to claim 52, wherein said filmy die-bonding material comprises polymide resin and epoxy resin.

68. (New) A process according to claim 53, wherein said filmy die-bonding material comprises polymide resin and epoxy resin.

69. (New) A process according to claim 54, wherein said filmy die-bonding material comprises polymide resin and epoxy resin.